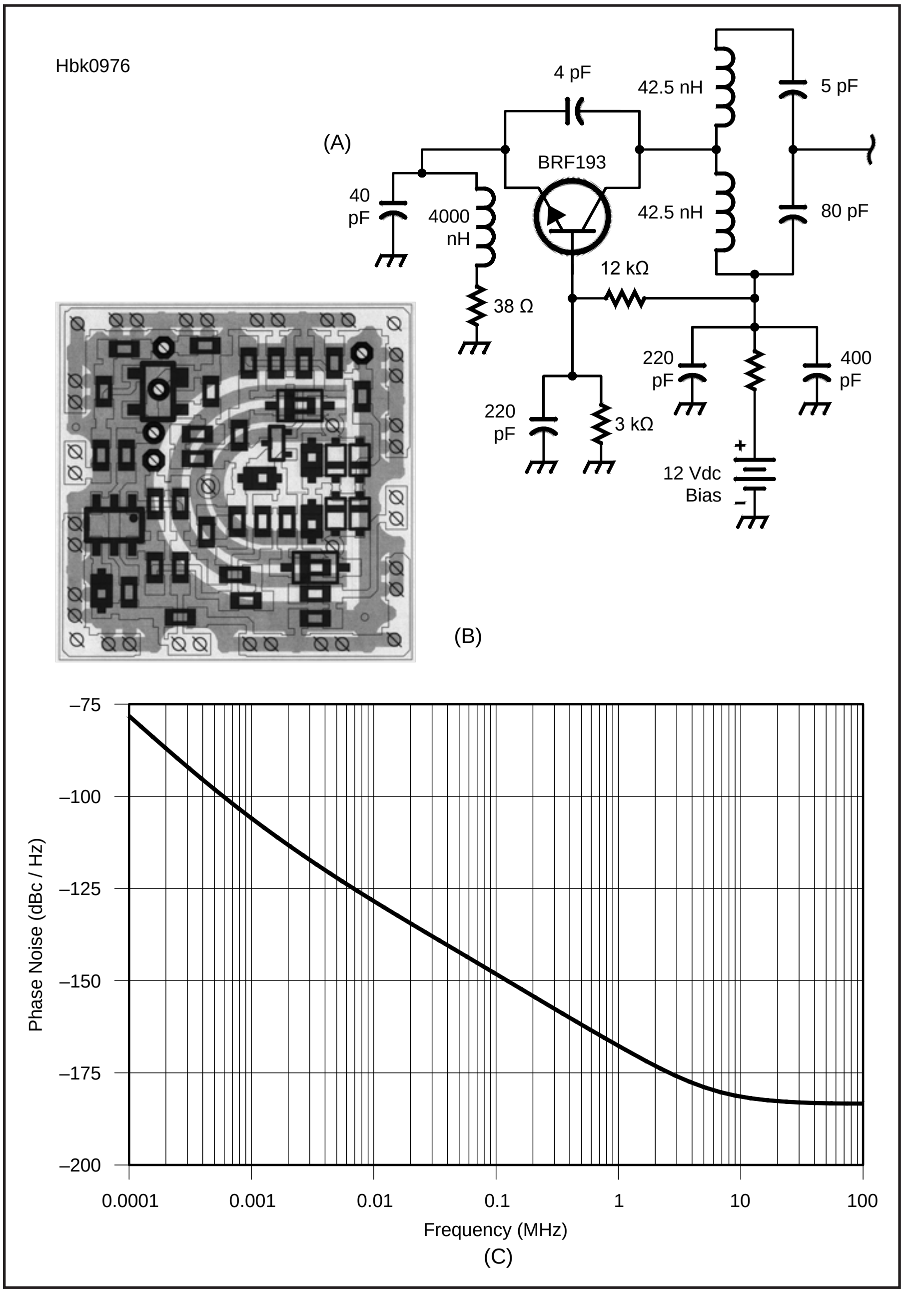

Figure 9.13 — 432 MHz oscillator circuit using tapped inductor and I_E = 30 mA (A), an example of the circuit layout using buried printed coupled line resonator (stripline resonator) in the middle layer of the board (B), and simulated phase noise plot (C).

ommended as more practical and gives better performance.

Because of the oscillator transistor's large capacitors from base to ground (220 pF) and collector to ground (680 pF), the various parameters of the oscillator transistor have little practical influence on circuit performance. The widely available 2N3904 performs well for both the oscillator and buffer transistors.

Practical resonator coil and the tuning capacitors will have a positive temperature coefficient. The 8 pF and the 18 pF capacitors should have an N150 temperature coefficient to partially compensate for their drift. After 1 hour, the observed frequency drift for this circuit was less than 10 Hz / hour.

THE K7HFD LOW-NOISE DIFFERENTIAL OSCILLATOR

The other high performance oscillator example, shown in **Figure 9.15**, is designed for low-noise performance by Linley Gumm, K7HFD, and appears on page 126 of the ARRL's *Solid State Design for the Radio Amateur* (out of print, but available used and through libraries). This circuit uses no unusual components and looks simple, yet it is a subtle and sophisticated circuit. (An analysis and simulation of this circuit by its designer is included in the downloadable supplemental material for this book.)

The effects of limiting in reducing AM oscillator noise were covered previously. However, because AM noise sidebands can get translated into PM noise sidebands by imperfect limiting, there is an advantage to stripping off the AM as early as possible, in the oscillator itself. An ALC system in the oscillator will counteract and cancel only the AM components within its bandwidth, but an oscillator based on a limiter will do this over a broad bandwidth. K7HFD's oscillator uses a differential pair of bipolar transistors as a limiting amplifier. The dc bias voltage at the bases and the resistor in the common emitter path to ground establishes a controlled dc bias current, here 25 to 27 mA. The ac voltage between the bases switches this current between the two collectors. This applies a rectangular pulse of current into link winding L2, which drives the series-resonant tank L1-C1. The output impedance of the collector is high in both the current-on and current-off states. Along with the small number of turns of the link winding, this presents very high impedance to the tank circuit, which minimizes degradation of the tank Q. The input impedance of this limiter is also quite high and is applied across only a one-turn tap of L1, which similarly minimizes any impact on the tank Q. The input transistor base is driven into conduction only on one peak of the tank waveform. The output transformer has the inverse of the current pulse applied to it, so the output is not a low distortion sine wave, although the output harmonics will not be as extensive as simple theory would suggest because the circuit's high output impedance allows stray capacitances to attenuate high-frequency components. The low-frequency transistors used here also act to reduce the harmonic power.

With an output of +17 dBm, this is a power oscillator, running with nearly 300 mW of dc input power, so appreciable heating is present that can cause temperature-induced drift. The circuit's high-power operation is a deliberate ploy to create a high signal-to-noise ratio by having as high a signal power as possible. This also reduces the problem of the oscillator's broadband noise output. The limitation on the signal level in the tank is the transistors' base-emitter-junction breakdown voltage. The circuit runs with a few volts peak-to-peak across the one-turn tap, so the full tank is running at over 50 V_{P-P}.

Excessive voltage levels for the transistors can easily be generated by this circuit. The single easiest way to damage a bipolar transistor is to reverse bias the base-emitter junction until it avalanches. Most devices are rated

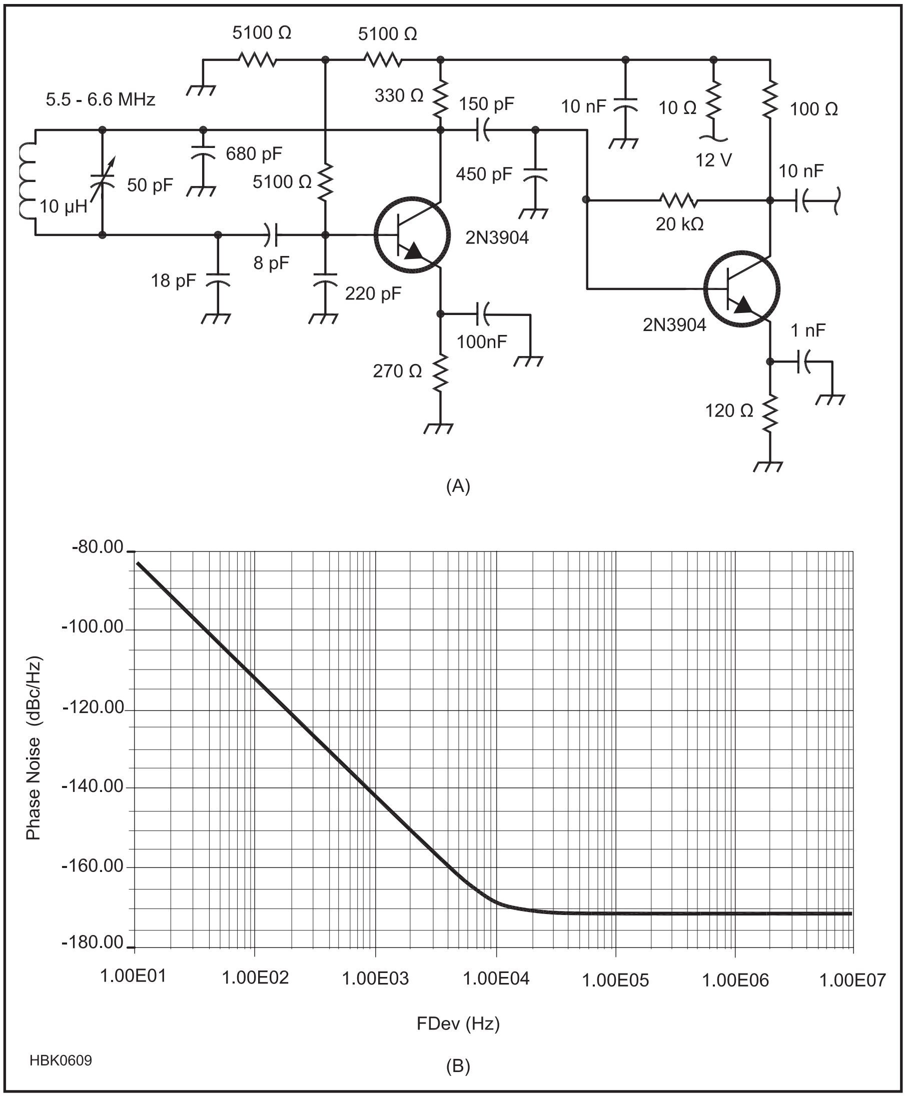

Figure 9.14 — At A, N1UL's Modified Vackar VFO is tuned from 5.5 to 6.6 MHz using the 50 pF capacitor. Tuning may be restricted to narrower ranges by placing a fixed capacitor in parallel with a smaller variable capacitor. The resonant frequency of the oscillator is determined by the 10 µH inductor and 50 pF tuning capacitor. B shows the excellent phase noise performance of the modified Vackar VFO in this *Harmonica* simulation. At 1 kHz from the carrier, noise is –144 dBc.

to withstand only 5 V applied this way, the current needed to do damage is small, and very little power is needed. If the avalanche current is limited to less than that needed to perform immediate destruction of the transistor, it is likely that there will be some degradation of the device, a reduction in its bandwidth and gain along with an increase in its noise. These changes are irreversible and cumulative. Small, fast signal diodes have breakdown voltages of over 30 V and less capacitance than the transistor bases, so one possible experiment would be to try the effect of adding a fast signal diode in series with the base of each transistor and running the circuit at even higher levels.

The oscillation amplitude is controlled by the drive current limit. The voltage on L2 must never allow the collector of the transistor driving it to go into saturation, for if this happens the transistor presents very low impedance to L2 and badly loads the tank, wrecking the Q and the noise performance. The circuit can be checked to verify the margin from saturation by probing the hot end of L2 and the emitter with an oscilloscope. Another, less obvious, test is to vary the power-supply voltage and monitor the output power. While the circuit is under current control, there is very little change in output power, but if the supply is low enough to allow saturation, the output power will change significantly with varying supply voltage.

The use of the 2N3904 is interesting, as it is not normally associated with RF oscillators. It is a cheap, plain, general-purpose type more often used at dc or audio frequencies. There is evidence that suggests some transistors that have good noise performance at RF have worse noise performance at low frequencies, and that the low-frequency noise they create can modulate an oscillator, creating noise sidebands. Experiments with low-noise audio transistors may be worthwhile, but many such devices have high junction capacitances.

In the description of this circuit in *Solid State Design for the Radio Amateur*, the results of a phase-noise test made using a spectrum analyzer with a crystal filter as a preselector are given. Ten kilohertz away from the carrier, in a 3 kHz measurement bandwidth, the noise was more than 120 dB below the carrier level. This translates into better than –120 – 10 log (3000), which equals –154.8 dBc/Hz, SSB, consistent with the modeled phase noise performance shown in Figure 9.15B. At this offset, –140 dBc is usually considered to be excellent. This VFO provides state-of-the art performance by today's standards — in a 1977 publication.

A JFET HARTLEY VFO

Figure 9.16 shows an 11.1 MHz version of a VFO and buffer closely patterned after that used in 7 MHz transceiver designs published by Roger Hayward, KA7EXM, and Wes Hayward, W7ZOI ("The Ugly Weekender") and Roy Lewallen, W7EL ("The Optimized QRP Transceiver"). In it, a Hartley oscillator using a 2N5486 JFET drives the two-2N3904 buffer attributed to Lewallen. This version diverges from the originals in that its JFET uses source bias (the bypassed 910 Ω resistor) instead of a gate-clamping diode and is powered from a low-current 7 V regulator IC instead of a Zener diode and dropping resistor. The 5 dB pad sets the buffer's output to a level appropriate for "Level 7" (+7 dBm LO) diode ring mixers.

The circuit shown was originally built with a gate-clamping diode, no source bias and a 3 dB output pad. Adjusting the oscillator bias as shown increased its output by 2 dB without degrading its frequency stability (200 to 300 Hz drift at power up, stability within ±20 Hz thereafter at a constant room temperature).

In recognition that precision mechanical tuning components are hard to obtain, the resonator uses "Bandset" and "Bandspread" variable capacitors. These terms are from the early days of radio: bandset is for coarse-tuning and bandspread is for fine-tuning.

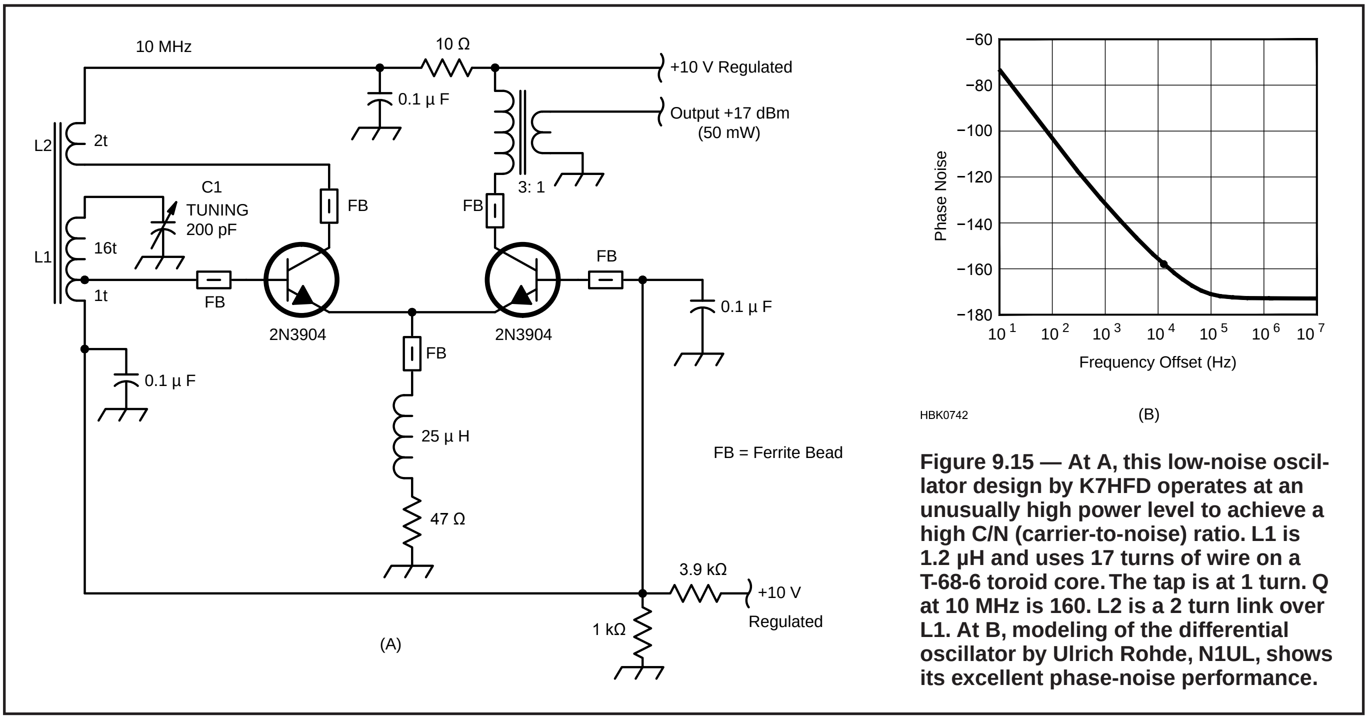

Figure 9.15 — At A, this low-noise oscillator design by K7HFD operates at an unusually high power level to achieve a high C/N (carrier-to-noise) ratio. L1 is 1.2 µH and uses 17 turns of wire on a T-68-6 toroid core. The tap is at 1 turn. Q at 10 MHz is 160. L2 is a 2 turn link over L1. At B, modeling of the differential oscillator by Ulrich Rohde, N1UL, shows its excellent phase-noise performance.

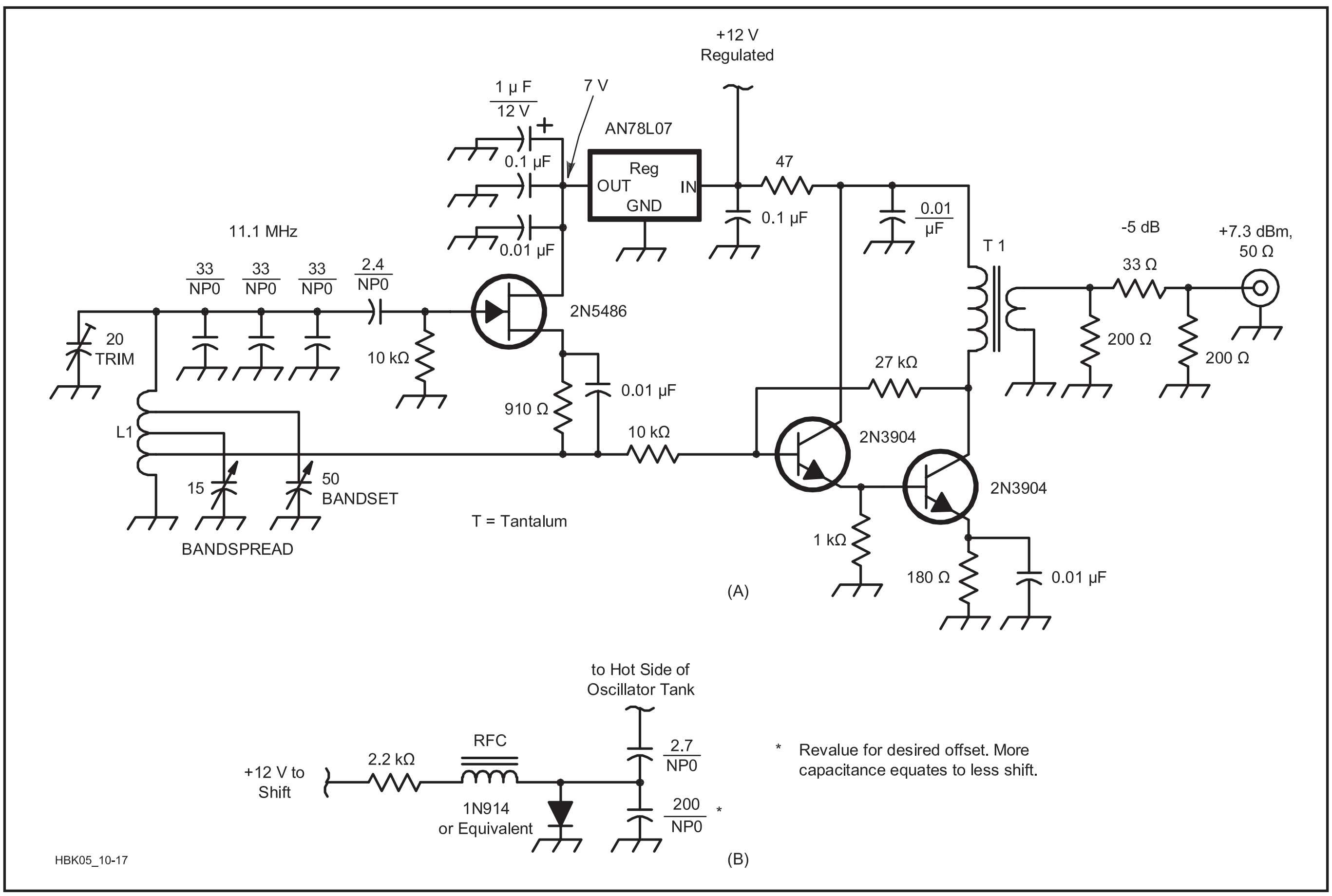

Figure 9.16 — Incorporating ideas from N1UL, KA7EXM, W7ZOI and W7EL, the oscillator at A achieves excellent stability and output at 11.1 MHz without the use of a gate-clamping diode, as well as end-running the shrinking availability of reduction drives through the use of bandset and bandspread capacitors. L1 consists of 10 turns of B & W #3041 Miniductor (#22 tinned wire, ⅝ inch in diameter, 24 turns per inch). The source tap is 2½ turns above ground; the tuning-capacitor taps are positioned as necessary for bandset and bandspread ranges required. T1's primary consists of 15 turns of #28 enameled wire on an FT-37-72 ferrite core; its secondary, 3 turns over the primary. B shows a system for adding fixed TR offset that can be applied to any LC oscillator. The RF choke consists of 20 turns of #26 enameled wire on an FT-37-43 core.